

[Signature] 8-1-1
Docket: 0756-2330

J1017 U.S. PRO
09/894125
06/29/01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Divisional Application of)
Shunpei YAMAZAKI et al.)
Based On Serial No. 09/352,198) Art Unit: 2823
Which Was Filed: July 13, 1999) Examiner: B. Kebede
For: CRYSTALLINE SEMICONDUCTOR THIN)
FILM, METHOD OF FABRICATING THE)
SAME, SEMICONDUCTOR DEVICE AND)
METHOD OF FABRICATING THE SAME) Date: June 29, 2001

INFORMATION DISCLOSURE STATEMENT
AND NOTIFICATION OF RELATED APPLICATIONS

Honorable Commissioner for Patents

Washington, D.C. 20231

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, it is requested that the references listed on the attached Form PTO-1449 be made of record in the above-identified application.

The references listed on the attached Form PTO-1449 were cited in parent application Serial No. 09/352,198 filed July 13, 1999.

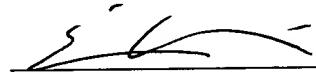
Copies of some of the references listed on PTO Form-1449 are submitted herewith in accordance with 37 C.F.R. 1.98(a).

The attention of the Examiner is directed to related application Serial No. 09/352,194. A copy the specification is enclosed herewith.

The Examiner's attention is also directed to two articles entitled: Aya et al., "Improvement of SPC poly-Si Film Using the ELA Method", September 11-12, 1997, pp. 167-170, AM-LCD; and Abe et al., High-Performance Poly-Crystalline

Silicon TFT's Fabricated Using the SPC and ELA Methods", July 9-10, 1998, pp. 85-88, AM-LCD.

Respectfully submitted,



Eric J. Robinson
Registration No. 38,285

NIXON PEABODY LLP
8180 Greensboro Drive, Suite 800
McLean, Virginia 22102
(703) 790-9110